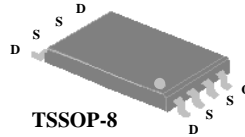




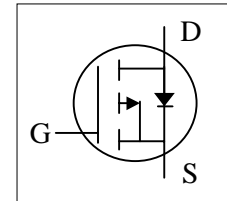
- ▼ Small & Thin Package
- ▼ Fast Switching Characteristic
- ▼ Capable of 1.8V Gate Drive



$BV_{DSS}$	-20V
$R_{DS(ON)}$	42m $\Omega$
$I_D$	-4.2A

## Description

The Advanced Power MOSFETs from APEC provide the designer with the best combination of fast switching, ruggedized device design, ultra low on-resistance and cost-effectiveness.



## Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	- 20	V
$V_{GS}$	Gate-Source Voltage	$\pm 8$	V
$I_D@T_A=25^\circ\text{C}$	Continuous Drain Current <sup>3</sup>	-4.2	A
$I_D@T_A=70^\circ\text{C}$	Continuous Drain Current <sup>3</sup>	-3.3	A
$I_{DM}$	Pulsed Drain Current <sup>1</sup>	-30	A
$P_D@T_A=25^\circ\text{C}$	Total Power Dissipation	1	W
	Linear Derating Factor	0.01	W/ $^\circ\text{C}$
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
$T_J$	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

## Thermal Data

Symbol	Parameter	Value	Unit
Rthj-a	Thermal Resistance Junction-ambient <sup>3</sup>	Max. 120	$^\circ\text{C}/\text{W}$
Rthj-L	Thermal Resistance Junction-lead	Max. 70	$^\circ\text{C}/\text{W}$


**Electrical Characteristics @ $T_j=25^\circ\text{C}$ (unless otherwise specified)**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=-250\mu A$	-20	-	-	V
$\Delta BV_{DSS}/\Delta T_j$	Breakdown Voltage Temperature Coefficient	Reference to $25^\circ\text{C}$ , $I_D=-1\text{mA}$	-	-0.01	-	$V/^\circ\text{C}$
$R_{DS(ON)}$	Static Drain-Source On-Resistance <sup>2</sup>	$V_{GS}=-4.5V, I_D=-4.0A$	-	-	42	$\text{m}\Omega$
		$V_{GS}=-2.5V, I_D=-4.0A$	-	-	52	$\text{m}\Omega$
		$V_{GS}=-1.8V, I_D=-3.0A$	-	-	70	$\text{m}\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=-250\mu A$	-0.3	-	-1	V
$g_{fs}$	Forward Transconductance	$V_{DS}=-5V, I_D=-4A$	-	4	-	S
$I_{DSS}$	Drain-Source Leakage Current ( $T_j=25^\circ\text{C}$ )	$V_{DS}=-20V, V_{GS}=0V$	-	-	-1	$\mu A$
	Drain-Source Leakage Current ( $T_j=70^\circ\text{C}$ )	$V_{DS}=-16V, V_{GS}=0V$	-	-	-25	$\mu A$
$I_{GSS}$	Gate-Source Leakage	$V_{GS}=\pm 8V$	-	-	$\pm 100$	nA
$Q_g$	Total Gate Charge <sup>2</sup>	$I_D=-4A$	-	21	34	nC
$Q_{gs}$	Gate-Source Charge	$V_{DS}=-10V$	-	6	-	nC
$Q_{gd}$	Gate-Drain ("Miller") Charge	$V_{GS}=-4.5V$	-	4.4	-	nC
$t_{d(on)}$	Turn-on Delay Time <sup>2</sup>	$V_{DS}=-10V$	-	13	-	ns
$t_r$	Rise Time	$I_D=-4A$	-	39	-	ns
$t_{d(off)}$	Turn-off Delay Time	$R_G=3.3\Omega, V_{GS}=-5V$	-	24	-	ns
$t_f$	Fall Time	$R_D=2.5\Omega$	-	72	-	ns
$C_{iss}$	Input Capacitance	$V_{GS}=0V$	-	1720	2752	pF
$C_{oss}$	Output Capacitance	$V_{DS}=-10V$	-	275	-	pF
$C_{rss}$	Reverse Transfer Capacitance	$f=1.0\text{MHz}$	-	215	-	pF

**Source-Drain Diode**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$V_{SD}$	Forward On Voltage <sup>2</sup>	$T_j=25^\circ\text{C}, I_S=-0.86A, V_{GS}=0V$	-	-	-1.2	V
$t_{rr}$	Reverse Recovery Time <sup>2</sup>	$I_S=-4A, V_{GS}=0V,$	-	23	-	ns
$Q_{rr}$	Reverse Recovery Charge	$dI/dt=100A/\mu s$	-	16	-	nC

**Notes:**

1. Pulse width limited by Max. junction temperature.
2. Pulse test.
3. Surface mounted on  $1\text{ in}^2$  copper pad of FR4 board  $t \leq 10s$ .

THIS PRODUCT IS ELECTROSTATIC SENSITIVE, PLEASE HANDLE WITH CAUTION.

THIS PRODUCT HAS BEEN QUALIFIED FOR USE IN CONSUMER APPLICATIONS. APPLICATIONS OR USE IN LIFE SUPPORT OR OTHER SIMILAR MISSION-CRITICAL DEVICES OR SYSTEMS ARE NOT AUTHORIZED.

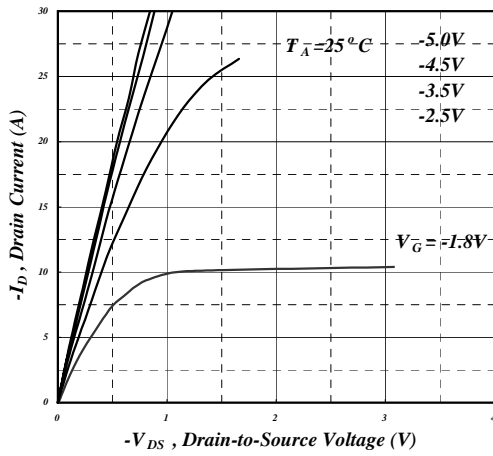


Fig 1. Typical Output Characteristics

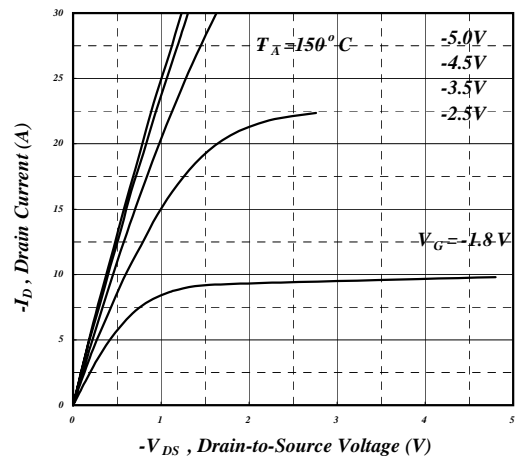


Fig 2. Typical Output Characteristics

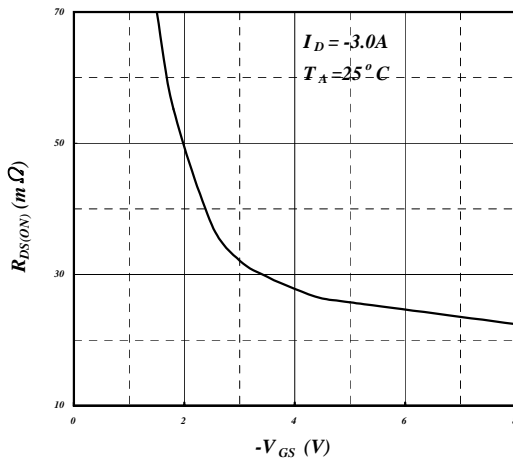


Fig 3. On-Resistance v.s. Gate Voltage

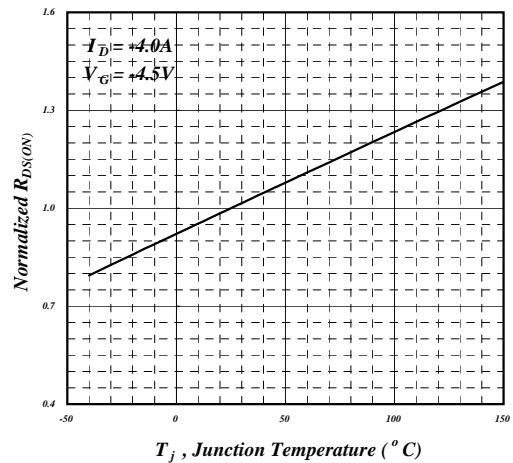


Fig 4. Normalized On-Resistance v.s. Junction Temperature

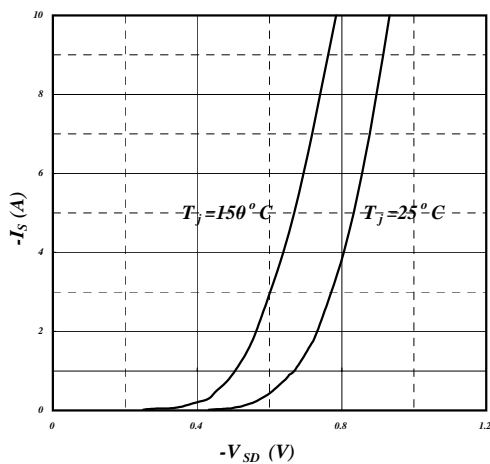


Fig 5. Forward Characteristic of Reverse Diode

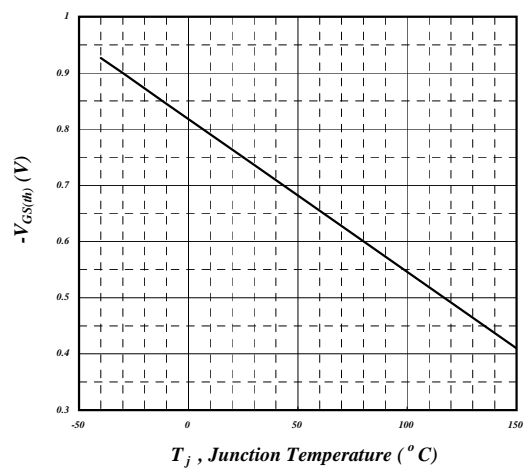


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

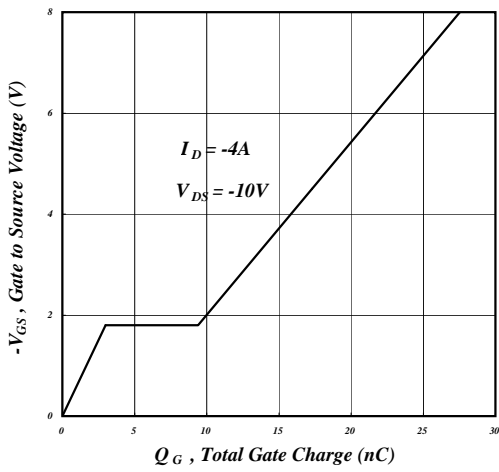


Fig 7. Gate Charge Characteristics

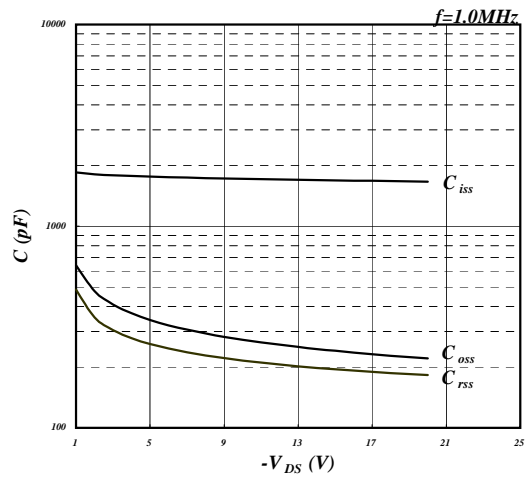


Fig 8. Typical Capacitance Characteristics

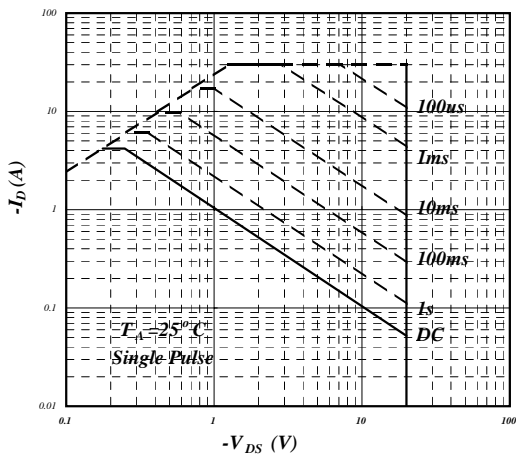


Fig 9. Maximum Safe Operating Area

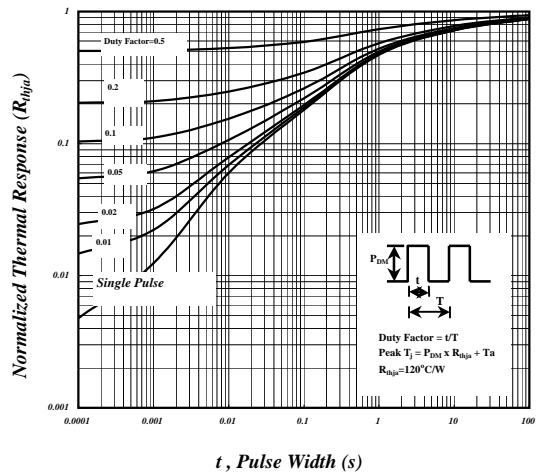


Fig 10. Effective Transient Thermal Impedance

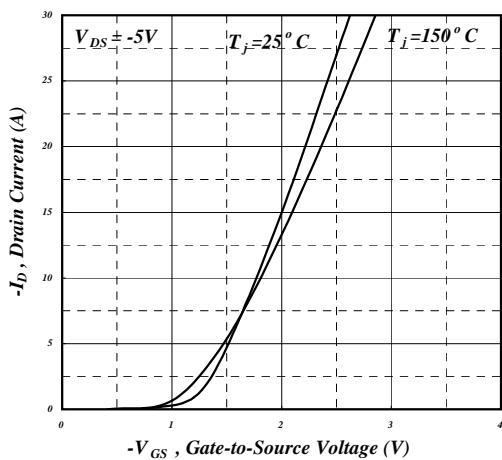


Fig 11. Transfer Characteristics

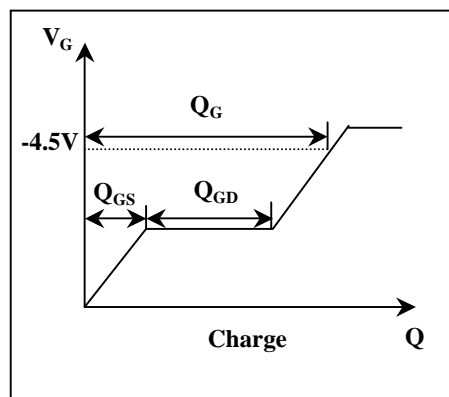


Fig 12. Gate Charge Waveform